

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a gate interconnection;

a source interconnection; and

an insulating film,

wherein the gate interconnection and the source interconnection are formed on and in direct contact with a same insulating plane, in a first region, and

wherein the gate interconnection and the source interconnection are formed over the same insulating plane with the insulating film interposed between the gate interconnection and the source interconnection, in the second region.

2. (Currently Amended) A semiconductor device comprising:

a gate interconnection;

a source interconnection; and

an island-like insulating film,

wherein the gate interconnection and the source interconnection are formed on and in direct contact with a same insulating plane, in a first region, and

wherein the gate interconnection and the source interconnection are formed over the same insulating plane with the island-like insulating film interposed between the gate interconnection and the source interconnection, in the second region.

3. (Currently Amended) A semiconductor device comprising:

a gate interconnection;

a source interconnection;

an island-like insulating film;

an active layer; [[and]]

a gate insulating film; and

a gate electrode,

wherein the gate interconnection and the source interconnection are formed on and in direct contact with a same insulating plane, in a first region,

wherein the gate interconnection and the source interconnection are formed over the same insulating plane with the island-like insulating film interposed between the gate interconnection and the source interconnection, in a second region,

wherein the active layer and the gate ~~interconnection~~ electrode are formed over the same insulating plane with the gate insulating film interposed between the active layer and the gate ~~interconnection~~ electrode, in a third region, and

wherein a thin film transistor is formed in the third region.

4. (Previously Presented) A semiconductor device according to any one of claims 2 and 3,

wherein the island-like insulating layer is formed so as to cover the gate interconnection in a second region, and

wherein the source interconnection is formed over the island-like insulating layer.

5. (Previously Presented) A semiconductor device according to any one of claims 2 and 3,

wherein the island-like insulating layer is formed so as to cover the source interconnection in a second region, and

wherein the gate interconnection is formed over the island-like insulating layer.

6. (Currently Amended) A semiconductor device comprising:

a source region;

a source interconnection;

an island-like insulating film;

an active layer; [[and]]

a gate insulating film; and

a gate electrode,

wherein the gate interconnection and the source interconnection are formed on and in direct contact with a same insulating plane, in a first region,

wherein the gate interconnection and the source interconnection are formed over the same insulating plane with the island-like insulating film interposed between the gate interconnection and the source interconnection , in a second region,

wherein the active layer and the gate ~~interconnection~~ electrode are formed over the same insulating plane with the gate insulating film interposed between the active layer and the gate ~~interconnection~~ electrode, in a third region,

wherein a thin film transistor is formed in the third region, and

wherein the active layer and the source interconnection is directly connected, in the third region.

7. (Previously Presented) A semiconductor device according to claim 6 wherein the active layer and the source interconnection are connected without through a contact hole.

8. (Previously presented) A semiconductor device according to any one of claims 1 to 3 wherein at least one of the gate interconnection and the source interconnection is formed by discharging a solution containing metal particles.

9. (Previously presented) A semiconductor device according to any one of claims 1 to 3 wherein at least one of the gate interconnection and the source interconnection is formed by discharging a solution containing metal elements.

10. (Previously presented) A semiconductor device according to claim 1 wherein the insulating film is formed by discharging a solution containing an insulating material.

11. (Previously presented) A semiconductor device according to any one of claims 2 and 3 wherein the island-like insulating layer is formed by discharging a solution containing an insulating material.

12. (Previously Presented) A semiconductor device according to Claims 3 and 6, wherein the active layer comprises a microcrystalline semiconductor.

13. (Previously Presented) A semiconductor device according to Claims 3 and 6, wherein the

active layer comprises an organic semiconductor.

14-20. (Canceled)

21. (Previously Presented) A display device including the semiconductor device according to any one of claims 1 to 3 and 6.

22. (Previously Presented) A digital still camera including the semiconductor device according to any one of claims 1 to 3 and 6.

23. (Previously Presented) A personal computer including the semiconductor device according to any one of claims 1 to 3 and 6.

24. (Previously Presented) A mobile computer including the semiconductor device according to any one of claims 1 to 3 and 6.

25. (Previously Presented) An image reproducing system including the semiconductor device according to any one of claims 1 to 3 and 6.